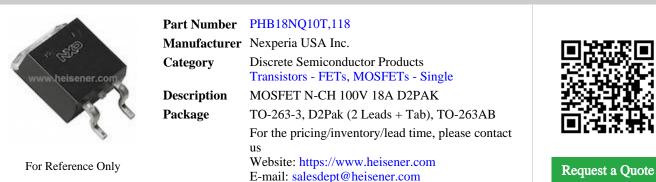


PHB18NQ10T,118

PHB18NQ10T,118 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



PHB18NQ10T,118 Specifications

Manufacturer Part Number	PHB18NQ10T,118	
Manufacturer	Nexperia USA Inc.	
Category	Discrete Semiconductor Products	
	Transistors - FETs, MOSFETs - Single	
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
Series	TrenchMOS?	
FET Type	N-Channel	
Technology	MOSFET (Metal Oxide)	
Drain to Source Voltage (Vdss)	100V	
Current - Continuous Drain (Id) @ 25°C	18A (Tc)	
Drive Voltage (Max Rds On, Min Rds On)	10V	
Vgs(th) (Max) @ Id	4V @ 1mA	
Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds	633pF @ 25V	
Vgs (Max)	$\pm 20 V$	
FET Feature	-	
Power Dissipation (Max)	79W (Tc)	
Rds On (Max) @ Id, Vgs	90 mOhm @ 9A, 10V	
Operating Temperature	-55°C ~ 175°C (TJ)	
Mounting Type	Surface Mount	
Supplier Device Package	D2PAK	
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
		Report errors?

PHB18NQ10T,118 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

PHB18NQ10T,118 Payment Methods



PHB18NQ10T,118 Shipping Methods



If you have any question about PHB18NQ10T,118, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com